

SURFACE PROTECTION ADHESIVE TAPE FOR SEMICONDUCTOR WAFER
BACKGRINDING, AND SEMICONDUCTOR WAFER GRINDING METHOD

ABSTRACT

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A surface-protective adhesive tape for back-grinding of a semiconductor wafer, comprising: a substrate; and a temporally adhesive layer provided on one side of the substrate, wherein a surface roughness R_z of the side of the substrate on which the temporally adhesive layer has not been formed is from 0.7 to 5.0 μm ,
10 wherein a total light transmittance of the surface-protective adhesive tape for back-grinding of the semiconductor wafer at an wavelength of 500 to 600 nm is from 40 to 80%, wherein a difference ($\Delta\text{ET}-\Delta\text{EM}$) between a color difference (ΔEM) of a mirror wafer and a color difference (ΔET) under a condition that the surface-protective adhesive tape for back-grinding of the semiconductor wafer
15 has been laminated on the mirror wafer is more than 6.5, and wherein the surface-protective adhesive tape for back-grinding of the semiconductor wafer is laminated on a surface of the semiconductor wafer having a notch and is used in the step of back-grinding of the semiconductor wafer; and a method of grinding a semiconductor wafer using the same.

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[Fig. 1]